

C3D16060D

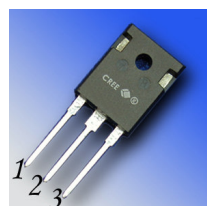
Silicon Carbide Schottky Diode

Z-REC™ RECTIFIER

V_{RRM}	=	600 V
I_F	=	16 A
	($T_c < 150^\circ\text{C}$)	
Q_c	=	42 nC

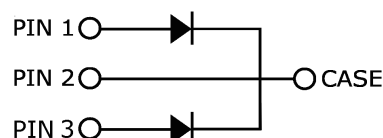
Features

- 600-Volt Schottky Rectifier
- Zero Reverse Recovery Current
- Zero Forward Recovery Voltage
- High-Frequency Operation
- Temperature-Independent Switching Behavior
- Extremely Fast Switching
- Positive Temperature Coefficient on V_F



Benefits

- Replace Bipolar with Unipolar Rectifiers
- Essentially No Switching Losses
- Higher Efficiency
- Reduction of Heat Sink Requirements
- Parallel Devices Without Thermal Runaway



Applications

- Switch Mode Power Supplies
- Power Factor Correction
- Solar Inverters
- Motor Drives
- Electric Vehicle Charger

Part Number	Package	Marking
C3D16060D	TO-247-3	C3D16060

Maximum Ratings ($T_c=25^\circ\text{C}$ unless otherwise specified)

Symbol	Parameter	Value	Unit	Test Conditions	Note
V_{RRM}	Repetitive Peak Reverse Voltage	600	V		
V_{RSM}	Surge Peak Reverse Voltage	600	V		
V_{DC}	DC Blocking Voltage	600	V		
I_F	Continuous Forward Current (Per Leg/Device)	8/16 10/20	A	$T_c < 150^\circ\text{C}$, No AC component $T_c < 135^\circ\text{C}$, No AC component	See Fig. 3
I_{FRM}	Repetitive Peak Forward Surge Current	57 36	A	$T_c = 25^\circ\text{C}$, $t_p = 10$ ms, Half Sine Wave, $D=0.3$ $T_c = 110^\circ\text{C}$, $t_p = 10$ ms, Half Sine Wave, $D=0.3$	
I_{FSM}	Non-Repetitive Peak Forward Surge Current	80 60	A	$T_c = 25^\circ\text{C}$, $t_p = 10$ mS, Half Sine Wave, $D=0.3$ $T_c = 110^\circ\text{C}$, $t_p = 10$ ms, Half Sine Wave, $D=0.3$	
I_{FSM}	Non-Repetitive Peak Forward Surge Current	220	A	$T_c = 25^\circ\text{C}$, $t_p = 10$ μs , Pulse	
P_{tot}	Power Dissipation (Per Leg)	100* 43*	W	$T_c = 25^\circ\text{C}$ $T_c = 110^\circ\text{C}$	
T_j, T_{stg}	Operating Junction and Storage Temperature	-55 to +175	$^\circ\text{C}$		
	TO-220 Mounting Torque	1 8.8	Nm lbf-in	M3 Screw 6-32 Screw	

* Per Leg, ** Per Device

Electrical Characteristics (Per Leg)

Symbol	Parameter	Typ.	Max.	Unit	Test Conditions	Note
V_F	Forward Voltage	1.6 1.9	1.8 2.4	V	$I_F = 8\text{ A}$ $T_J = 25^\circ\text{C}$ $I_F = 8\text{ A}$ $T_J = 175^\circ\text{C}$	
I_R	Reverse Current	10 20	50 200	μA	$V_R = 600\text{ V}$ $T_J = 25^\circ\text{C}$ $V_R = 600\text{ V}$ $T_J = 175^\circ\text{C}$	
Q_C	Total Capacitive Charge	21		nC	$V_R = 600\text{ V}$, $I_F = 8\text{ A}$ $di/dt = 500\text{ A}/\mu\text{s}$ $T_J = 25^\circ\text{C}$	
C	Total Capacitance	441 39 33		pF	$V_R = 0\text{ V}$, $T_J = 25^\circ\text{C}$, $f = 1\text{ MHz}$ $V_R = 200\text{ V}$, $T_J = 25^\circ\text{C}$, $f = 1\text{ MHz}$ $V_R = 400\text{ V}$, $T_J = 25^\circ\text{C}$, $f = 1\text{ MHz}$	

Note:

1. This is a majority carrier diode, so there is no reverse recovery charge.

Thermal Characteristics

Symbol	Parameter	Typ.	Unit
$R_{\theta JC}$	Thermal Resistance from Junction to Case	1.5 * 0.75 **	$^\circ\text{C}/\text{W}$

* Per Leg, ** Per Device

Typical Performance (Per Leg)

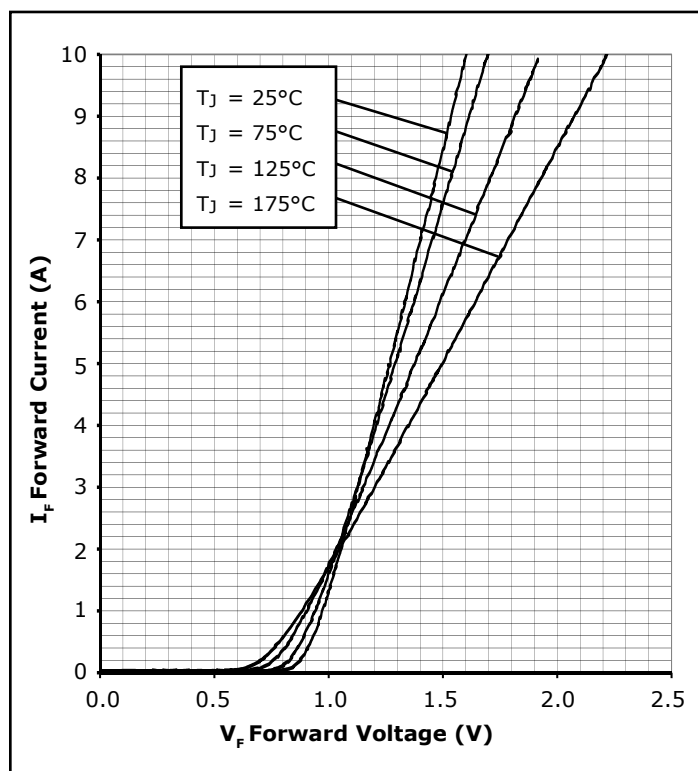


Figure 1. Forward Characteristics

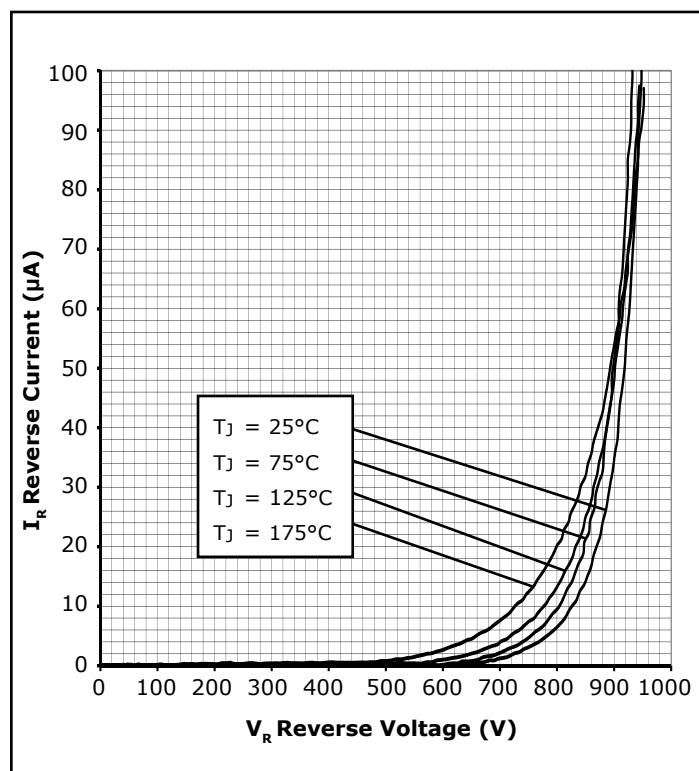


Figure 2. Reverse Characteristics

Typical Performance (Per Leg)

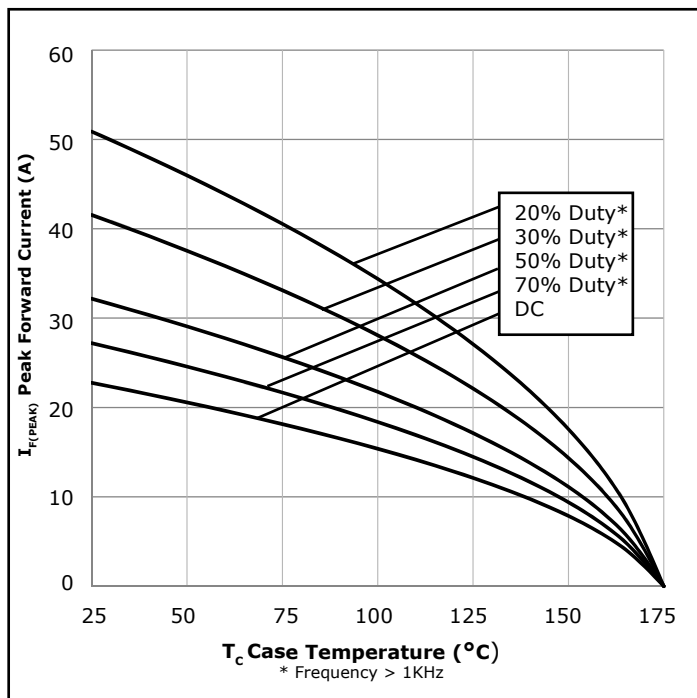


Figure 3. Current Derating

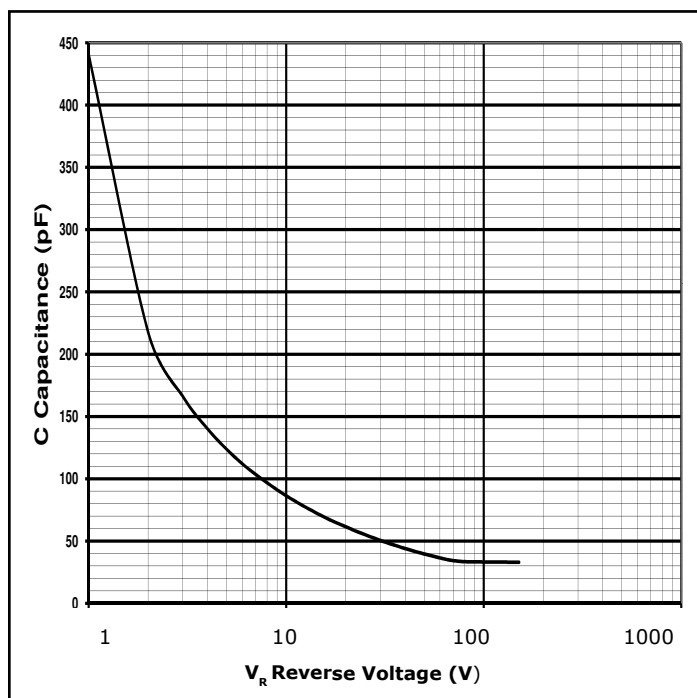


Figure 4. Capacitance vs. Reverse Voltage

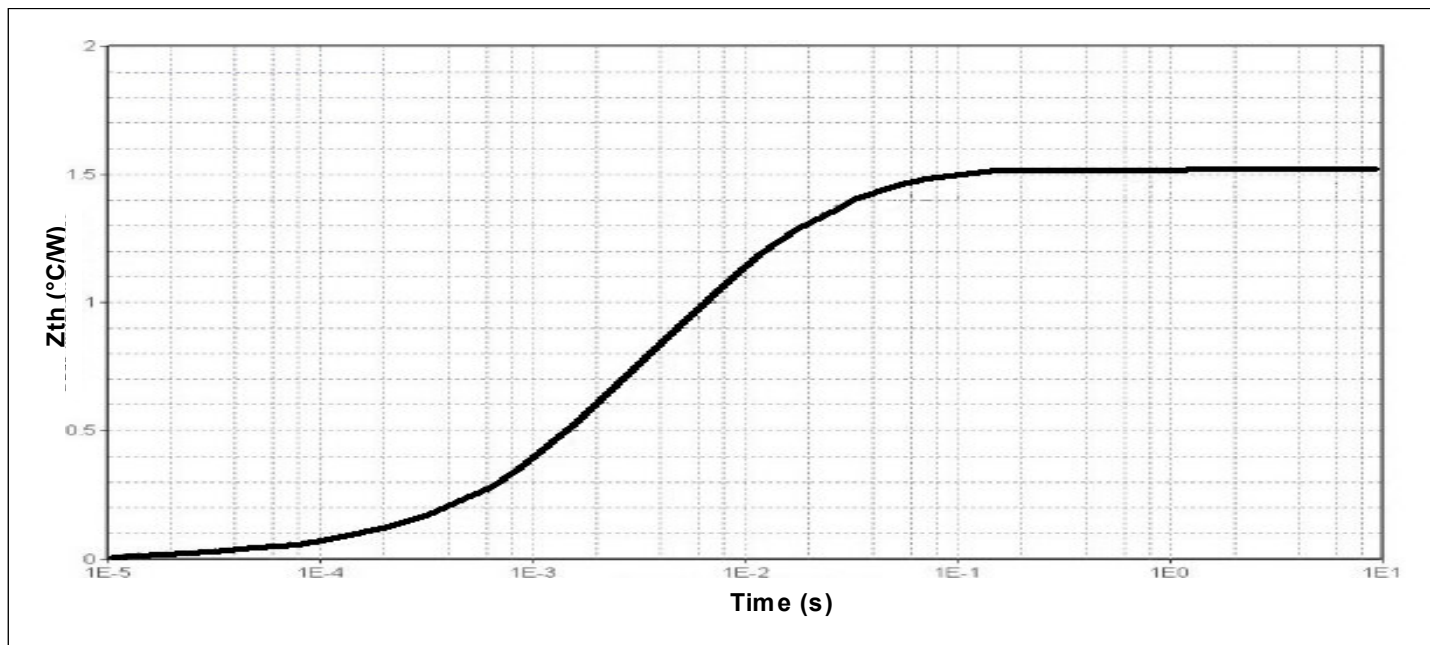


Figure 5. Transient Thermal Impedance

Typical Performance (Per Leg)

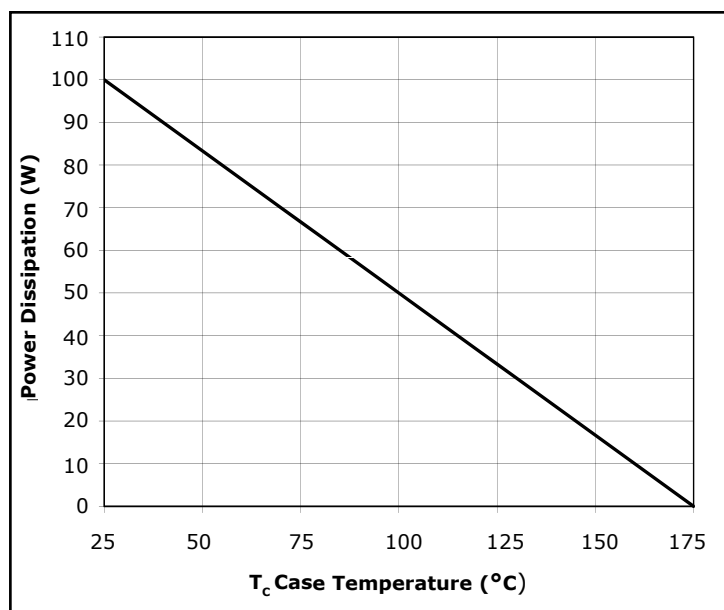
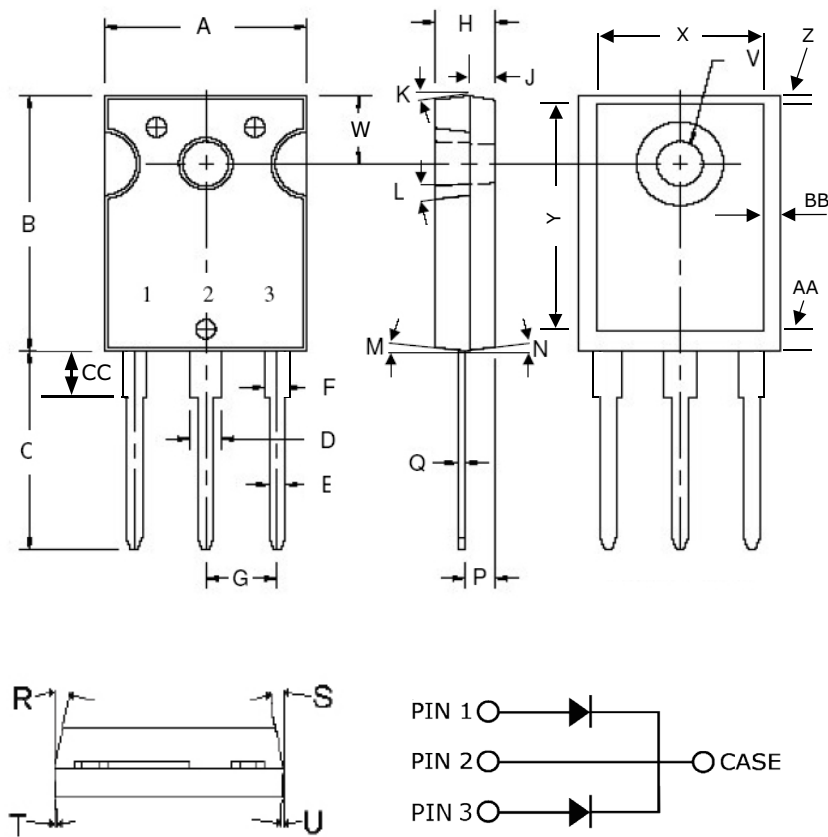


Figure 6. Power Derating

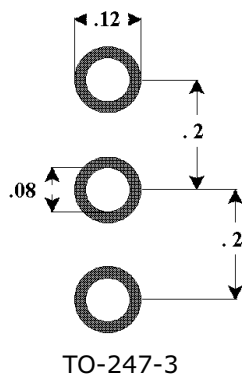
Package Dimensions

Package TO-247-3

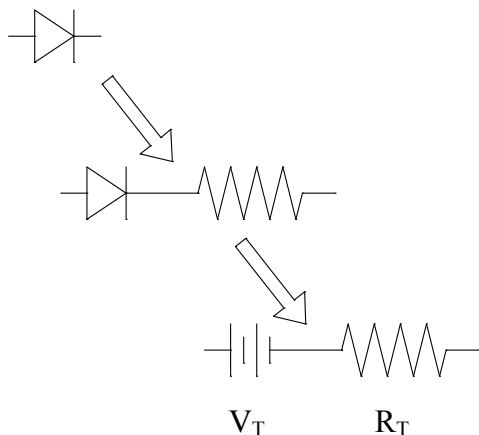


POS	Inches		Millimeters	
	Min	Max	Min	Max
A	.605	.635	15.367	16.130
B	.800	.831	20.320	21.10
C	.780	.800	19.810	20.320
D	.095	.133	2.413	3.380
E	.046	.052	1.168	1.321
F	.060	.095	1.524	2.410
G	.215 TYP		5.460 TYP	
H	.175	.205	4.450	5.210
J	.075	.085	1.910	2.160
K	6°	21°	6°	21°
L	4°	6°	4°	6°
M	2°	4°	2°	4°
N	2°	4°	2°	4°
P	.090	.100	2.286	2.540
Q	.020	.030	.508	.762
R	9°	11°	9°	11°
S	9°	11°	9°	11°
T	2°	8°	2°	8°
U	2°	8°	2°	8°
V	.137	.144	3.487	3.658
W	.210	.248	5.334	6.300
X	.502	.557	12.751	14.150
Y	.637	.695	16.180	17.653
Z	.038	.052	0.964	1.321
AA	.110	.140	2.794	3.556
BB	.030	.046	0.766	1.168
CC	.161	.176	4.100	4.472

Recommended Solder Pad Layout



Diode Model (Per Leg)



$$V_{f_T} = V_T + I_f \cdot R_T$$

$$V_T = 0.93 + (T_j \cdot -9.3 \cdot 10^{-4})$$

$$R_T = 0.058 + (T_j \cdot 5.7 \cdot 10^{-4})$$

Note: T_j = Diode Junction Temperature In Degrees Celcius

"The levels of environmentally sensitive, persistent biologically toxic (PBT), persistent organic pollutants (POP), or otherwise restricted materials in this product are below the maximum concentration values (also referred to as the threshold limits) permitted for such substances, or are used in an exempted application, in accordance with EU Directive 2002/95/EC on the restriction of the use of certain hazardous substances in electrical and electronic equipment (RoHS), as amended through April 21, 2006.

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